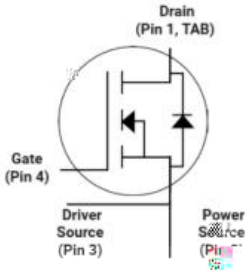
SG2M035120UJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-
-
-





Benefits

-
-
-
-
-





Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on),\ typ}$	$T_{J,max}$	Marking	Package

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1 Maximum ratings

Table 2 Maximum rating

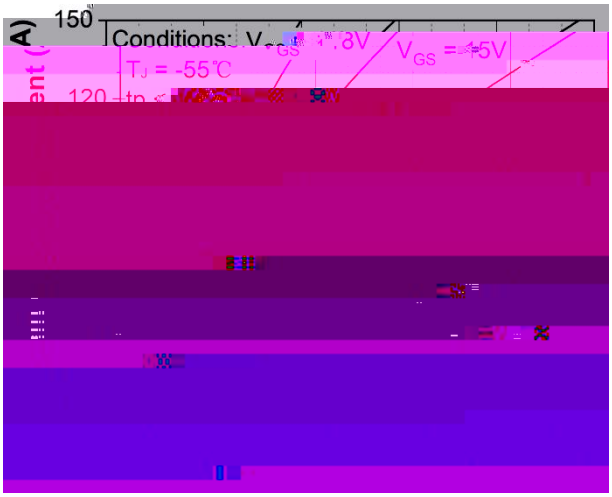
Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	

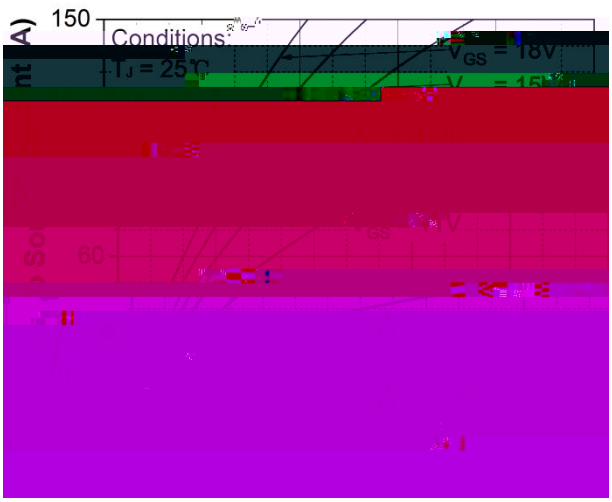


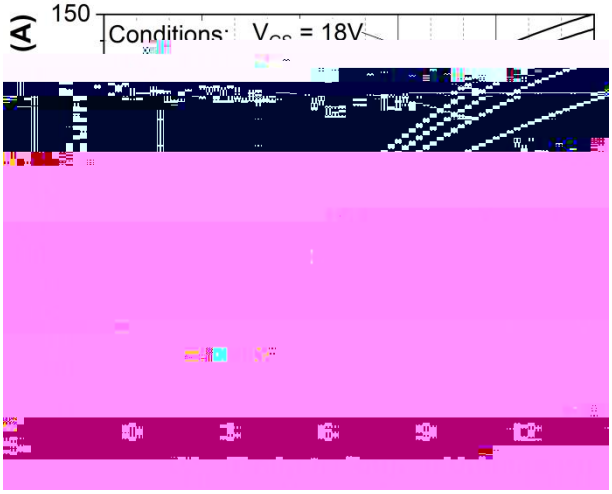
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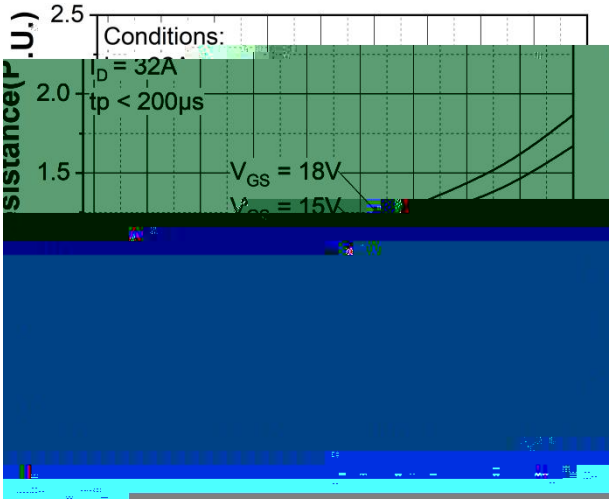
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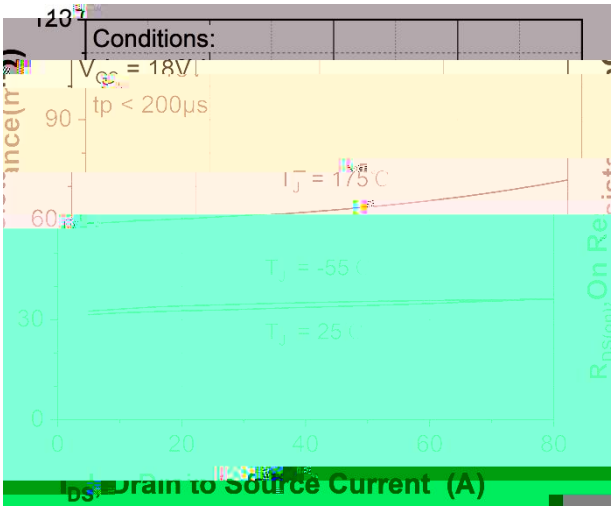
4 Electrical characteristic diagrams

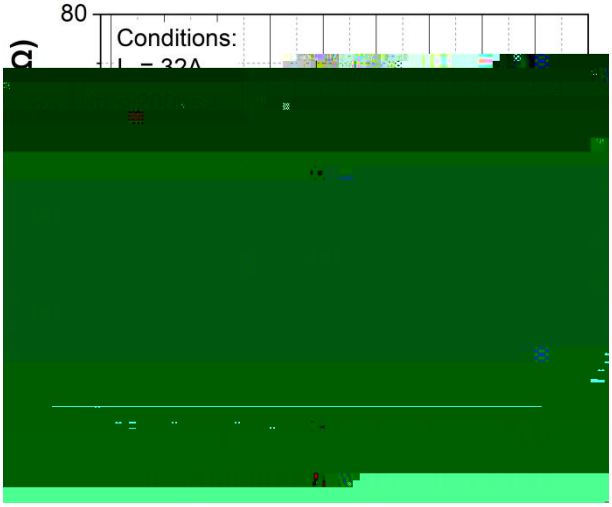




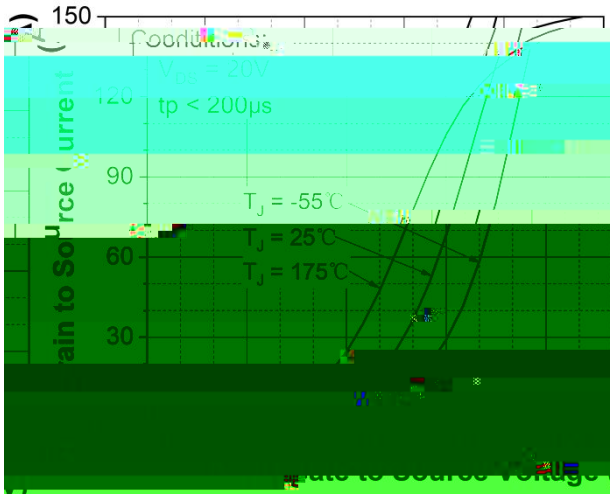


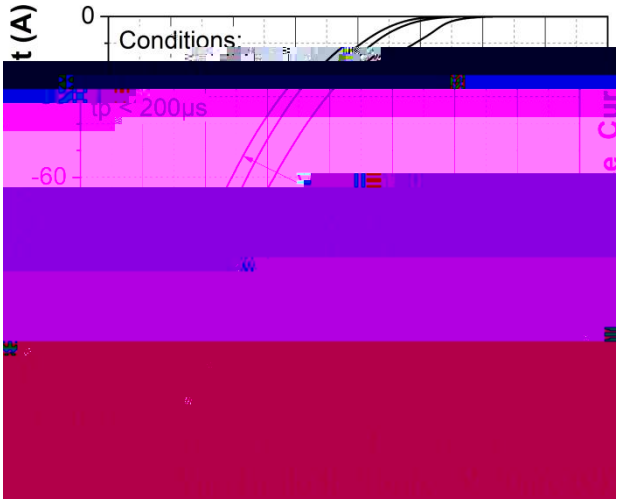


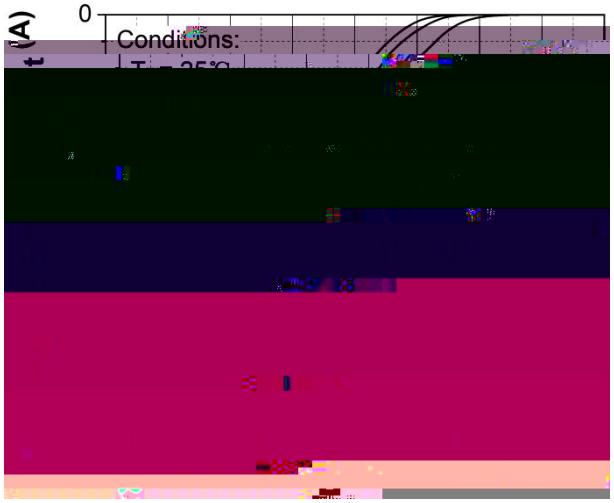


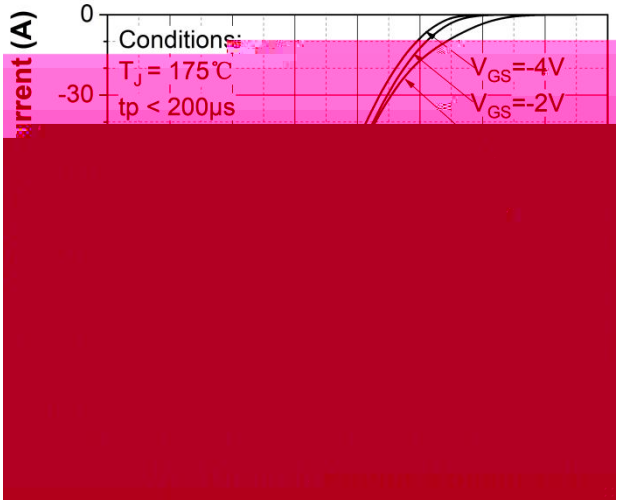


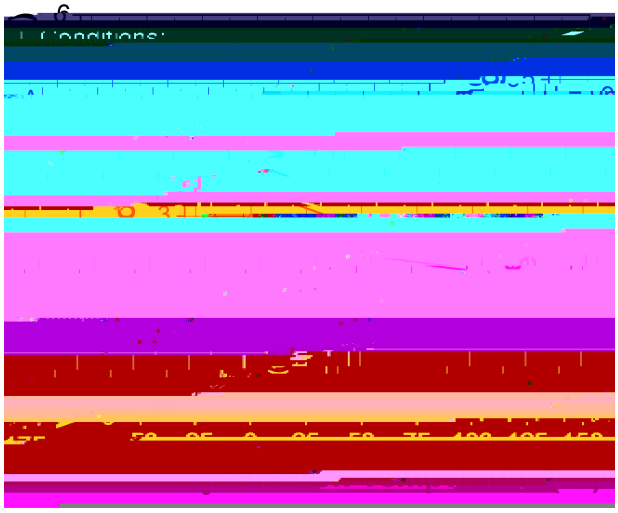
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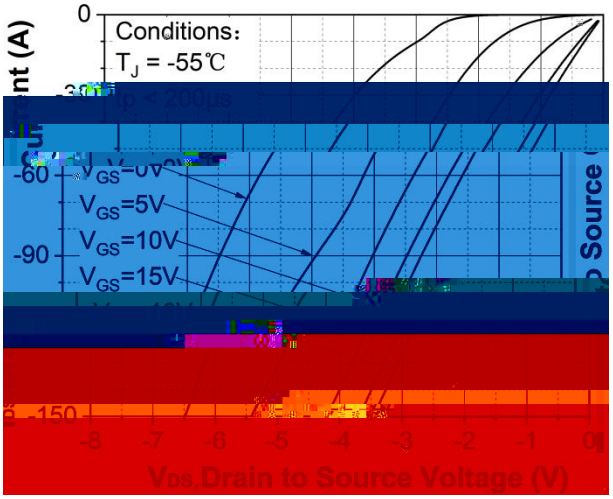


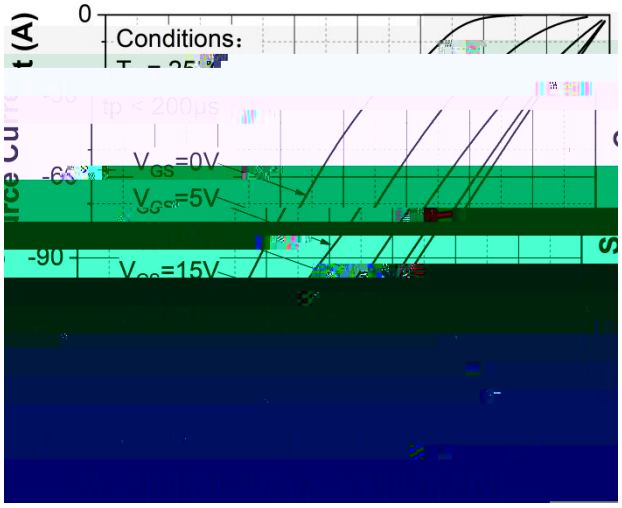


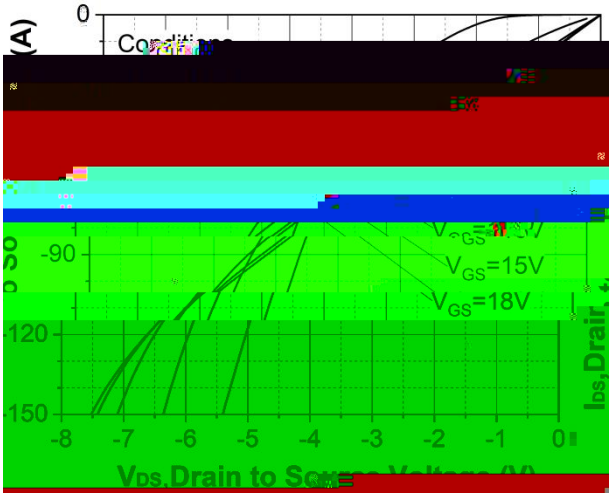




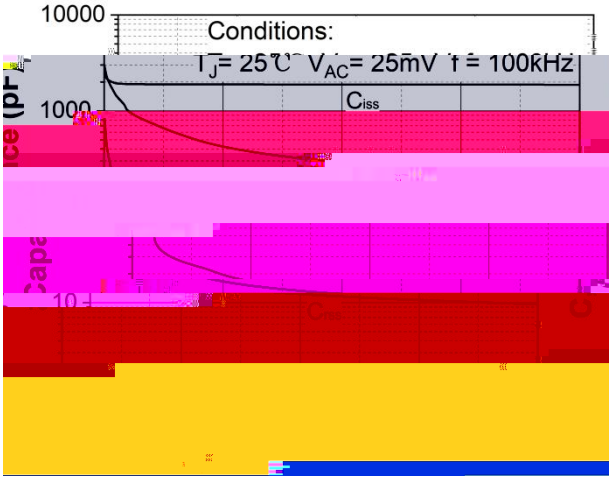
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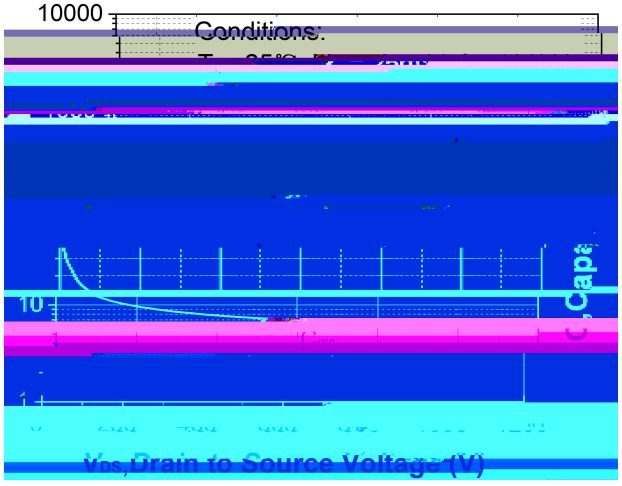






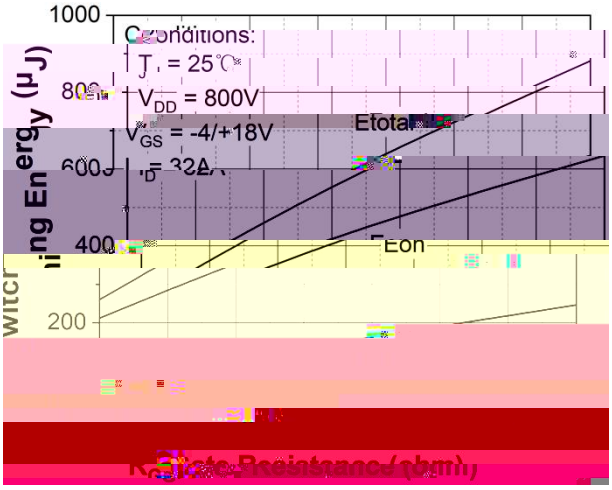


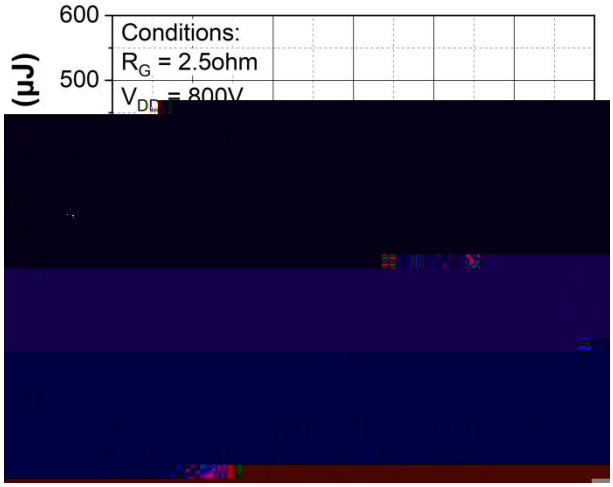


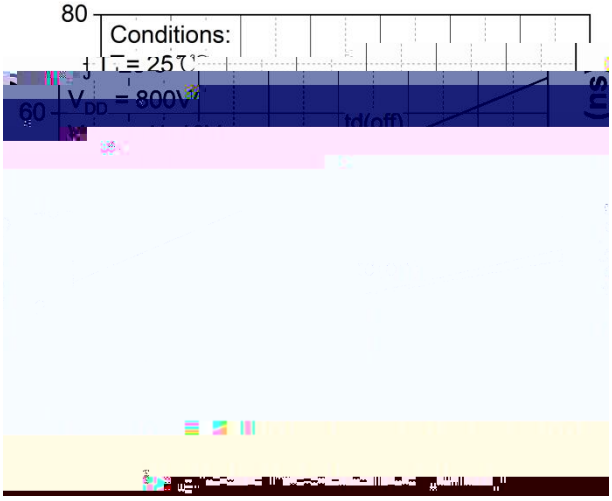


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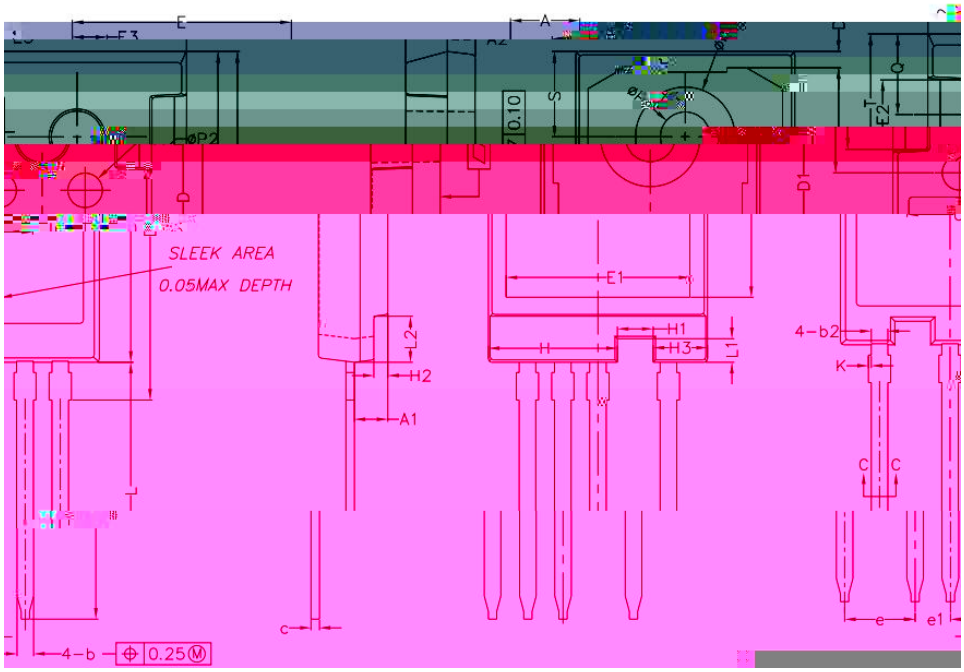
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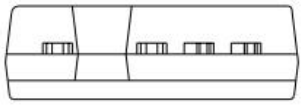


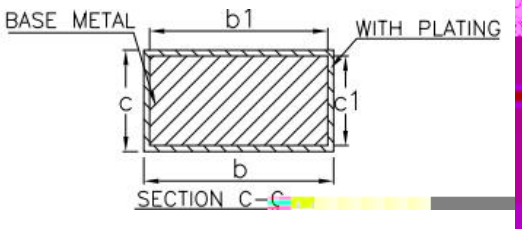




5 Package drawing



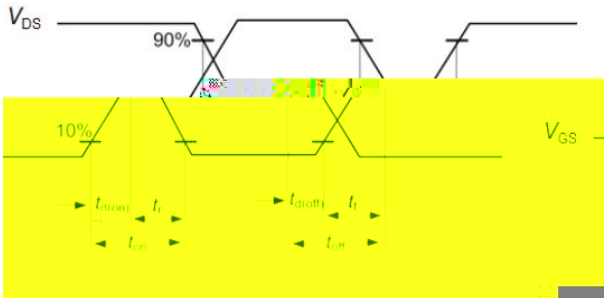


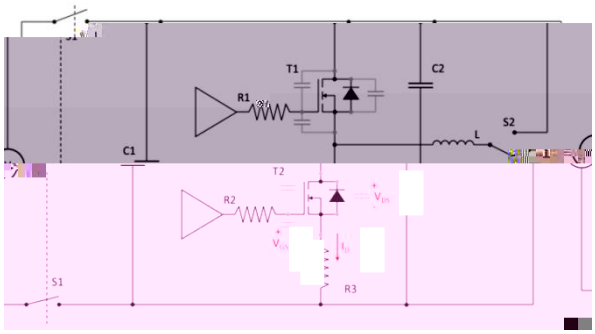


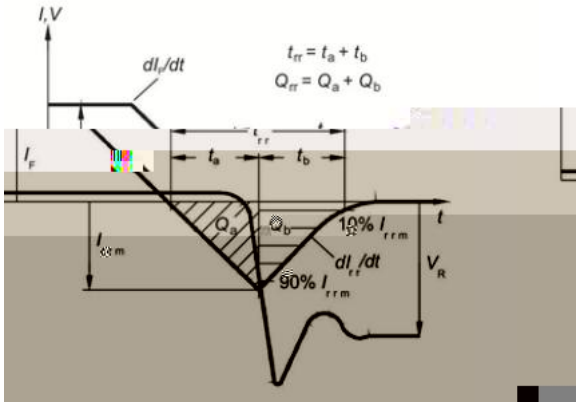
COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN		MAX
A	4.90	5.00	5.10
A1	2.37	2.47	2.57
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	1.16	-	1.29
c	0.59		0.66
c1	0.58	0.60	0.62
D	22.30	22.40	22.50
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	4.98	5.08	5.18
e1	2.44	2.54	2.64
H	9.20		
H1	2.48	2.58	2.68
H2	0.90	1.00	1.10
H3	3.82	3.92	4.02
K	0	-	0.20
L	18.40	18.52	18.70
L1	1.60	1.70	1.80

6 Test conditions







SG2M035120UJ

1200V SiC Power MOSFET

Revision history

Document versio

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